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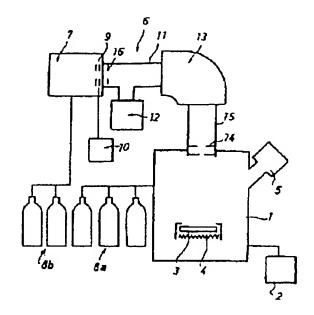
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TITLE

: ION COMPOSITE CVD METHOD AND

**DEVICE THEREFOR** 



ABSTRACT: PURPOSE: To simultaneously use a CVD method and ion implantation.

CONSTITUTION: The thin film is formed on a base plate in a low pressure region by a CVD method and also ions are implanted into this film at high speed through a differential pressure regulating means. Ion mixing or high-speed neutral particles are made incident on the film. Further this device is equipped with both a vacuum vessel 1 for forming the film on the base plate by a CVD method and an ion implantation device 6 described below. This ion implantation device 6 is connected to the vacuum vessel 1 via a differential pressure exhaust part and used for irradiating the film on the base plate 3 during film formation due to the CVD method with high-speed ions and high-speed neutral particles.

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